
2SK3212

Silicon N Channel MOS FET
High Speed Power Switching

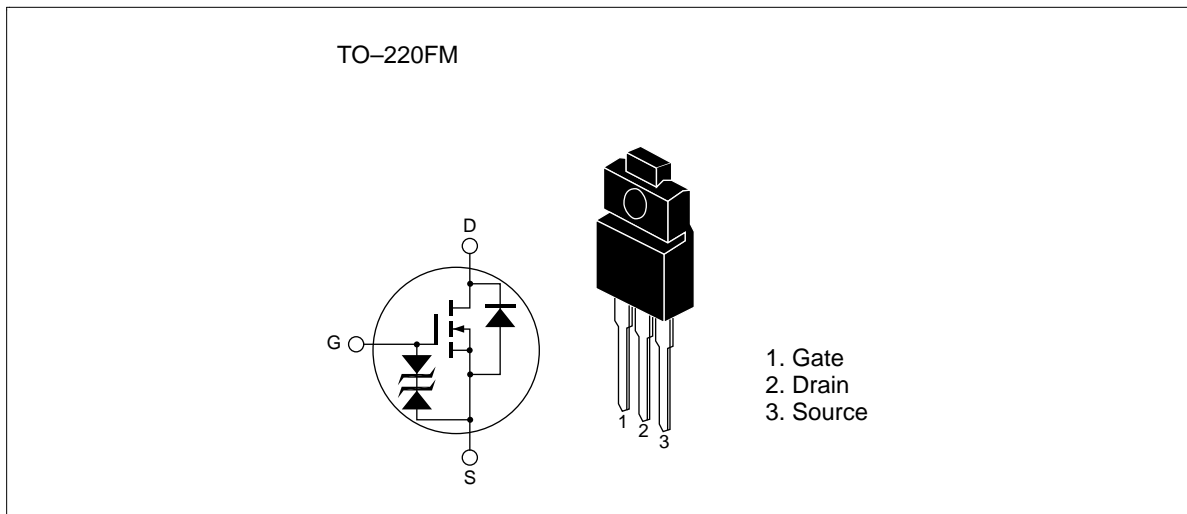
HITACHI

ADE-208-762(Z)
1st. Edition
Dec. 1, 1998

Features

- Low on-resistance
 $R_{DS} = 0.1\Omega$ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	10	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	40	A
Body-drain diode reverse drain current	I_{DR}	10	A
Avalanche current	I_{AP} ^{Note3}	10	A
Avalanche energy	E_{AR} ^{Note3}	10	mJ
Channel dissipation	P_{ch} ^{Note2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$
3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50\Omega$

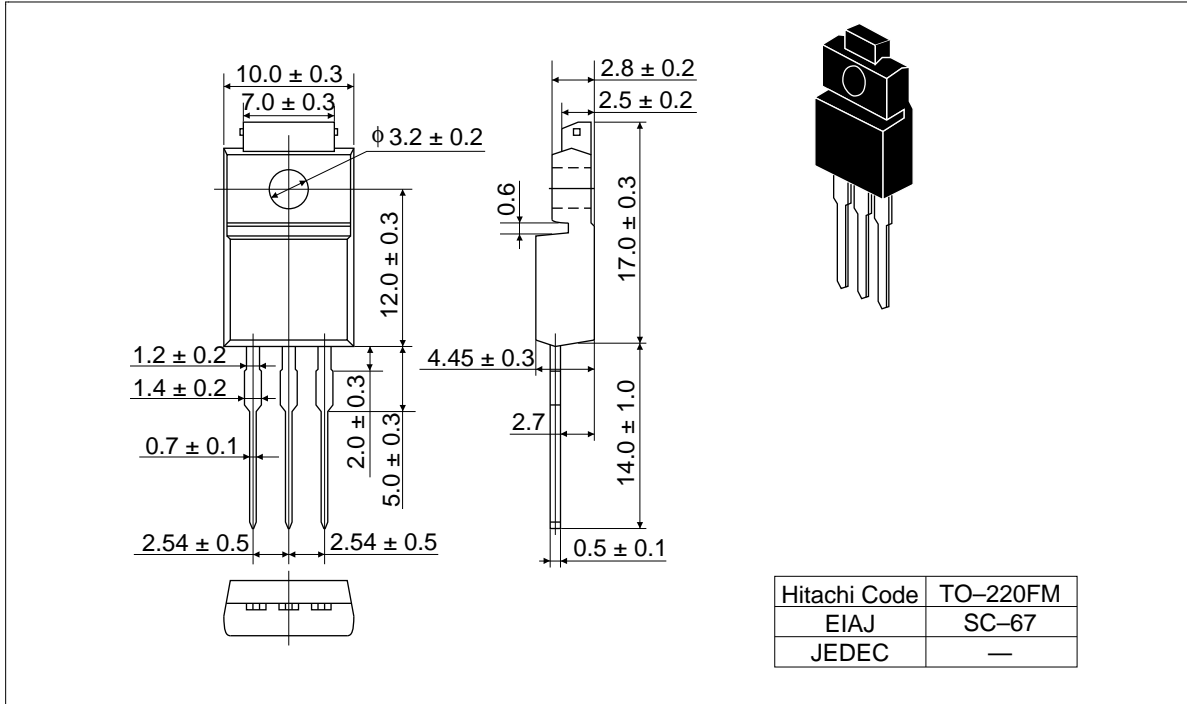
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10\text{mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 100\text{V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1\text{mA}, V_{DS} = 10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.1	0.13	Ω	$I_D = 5\text{A}, V_{GS} = 10\text{V}^{\text{Note4}}$
	$R_{DS(on)}$	—	0.13	0.18	Ω	$I_D = 5\text{A}, V_{GS} = 4\text{V}^{\text{Note4}}$
Forward transfer admittance	$ y_{fs} $	4.5	7.5	—	S	$I_D = 5\text{A}, V_{DS} = 10\text{V}^{\text{Note4}}$
Input capacitance	C_{iss}	—	420	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	—	185	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	100	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$I_D = 5\text{A}, V_{GS} = 10\text{V}$
Rise time	t_r	—	60	—	ns	$R_L = 10\Omega$
Turn-off delay time	$t_{d(off)}$	—	105	—	ns	
Fall time	t_f	—	70	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 10\text{A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	90	—	ns	$I_F = 10\text{A}, V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

Note: 4. Pulse test

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Package Dimensions (Unit: mm)



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